

EconoPACK™2 module with TRENCHSTOP™ IGBT7 and Emitter Controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 150\text{ A} / I_{CRM} = 300\text{ A}$
 - LOW V_{CESat}
 - Overload operation up to 175°C
 - TRENCHSTOP™ IGBT7
- Mechanical features
 - Integrated NTC temperature sensor
 - High power and thermal cycling capability
 - Solder contact technology
 - Al_2O_3 substrate with low thermal resistance
 - Copper base plate



Potential applications

- Motor drives
- Auxiliary inverters
- Servo drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

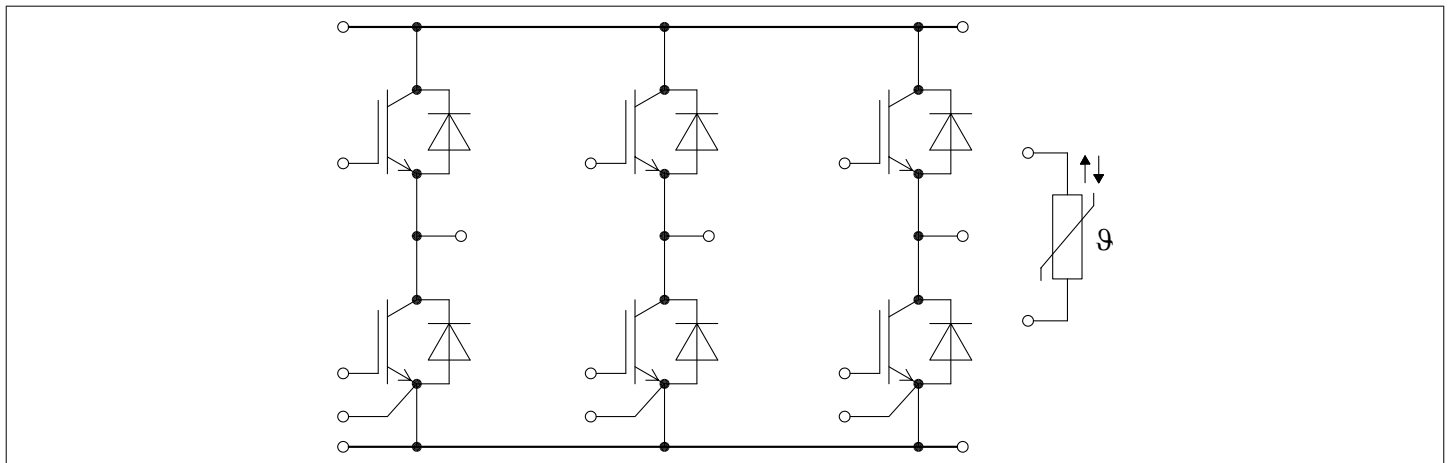


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1 Package

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal Isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		> 200	
RTI Elec.	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			25		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$, per switch		1.8		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for modul mounting	M	- Mounting according to valid application note	3		6	Nm
Weight	G			180		g

Note: The current under continuous operation is limited to 50A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175^\circ\text{C}$ $T_C = 80^\circ\text{C}$	150	A
Repetitive peak collector current	I_{CRM}	$t_p = 1 \text{ ms}$	300	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 150\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.55	1.80	V
			$T_{vj} = 125\ ^\circ C$		1.69		
			$T_{vj} = 175\ ^\circ C$		1.77		
Gate threshold voltage	V_{GEth}	$I_C = 3.5\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$			2.5		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			1		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			30.1		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.105		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.0012	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 150\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 3.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.157		μs
			$T_{vj} = 125\ ^\circ C$		0.170		
			$T_{vj} = 175\ ^\circ C$		0.177		
Rise time (inductive load)	t_r	$I_C = 150\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 3.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.065		μs
			$T_{vj} = 125\ ^\circ C$		0.071		
			$T_{vj} = 175\ ^\circ C$		0.074		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 150\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 3.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.336		μs
			$T_{vj} = 125\ ^\circ C$		0.414		
			$T_{vj} = 175\ ^\circ C$		0.457		
Fall time (inductive load)	t_f	$I_C = 150\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 3.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.100		μs
			$T_{vj} = 125\ ^\circ C$		0.189		
			$T_{vj} = 175\ ^\circ C$		0.251		
Turn-on energy loss per pulse	E_{on}	$I_C = 150\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 3.5\ \Omega, di/dt = 1500\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		21.1		mJ
			$T_{vj} = 125\ ^\circ C$		29.9		
			$T_{vj} = 175\ ^\circ C$		33.3		
Turn-off energy loss per pulse	E_{off}	$I_C = 150\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 3.5\ \Omega, dv/dt = 3250\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		9.65		mJ
			$T_{vj} = 125\ ^\circ C$		15.1		
			$T_{vj} = 175\ ^\circ C$		18.6		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_P \leq 8\ \mu s, T_{vj} = 150\ ^\circ C$		480		A
			$t_P \leq 7\ \mu s, T_{vj} = 175\ ^\circ C$		450		

Table 4 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.293	K/W
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W/(m}^2\text{K)}$		0.129		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC forward current	I_F			150	A
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$		300	A
I^2t - value	I^2t	$t_P = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125^\circ\text{C}$	2700	A^2s
			$T_{vj} = 175^\circ\text{C}$	2250	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 150 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		1.72	V
			$T_{vj} = 125^\circ\text{C}$		1.59	
			$T_{vj} = 175^\circ\text{C}$		1.52	
Peak reverse recovery current	I_{RM}	$V_R = 600 \text{ V}, I_F = 150 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1500 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		52.4	A
			$T_{vj} = 125^\circ\text{C}$		68.8	
			$T_{vj} = 175^\circ\text{C}$		79.6	
Recovered charge	Q_r	$V_R = 600 \text{ V}, I_F = 150 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1500 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$	$T_{vj} = 25^\circ\text{C}$		15.1	μC
			$T_{vj} = 125^\circ\text{C}$		24.2	
			$T_{vj} = 175^\circ\text{C}$		31.1	

Table 6 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Reverse recovery energy	E_{rec}	$V_R = 600 \text{ V}$, $I_F = 150 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 1500 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ °C}$)	$T_{vj} = 25 \text{ °C}$	4.98		mJ
			$T_{vj} = 125 \text{ °C}$	7.28		
			$T_{vj} = 175 \text{ °C}$	9.12		
Thermal resistance, junction to case	R_{thJC}	per diode			0.454	K/W
Thermal resistance, case to heatsink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}^2\text{K})$		0.140		K/W
Temperature under switching conditions	$T_{vj op}$		-40		175	°C

Note: $T_{vj op} > 150 \text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 NTC-Thermistor

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ °C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ °C}$, $R_{100} = 493 \text{ Ω}$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

Note: Specification according to the valid application note.

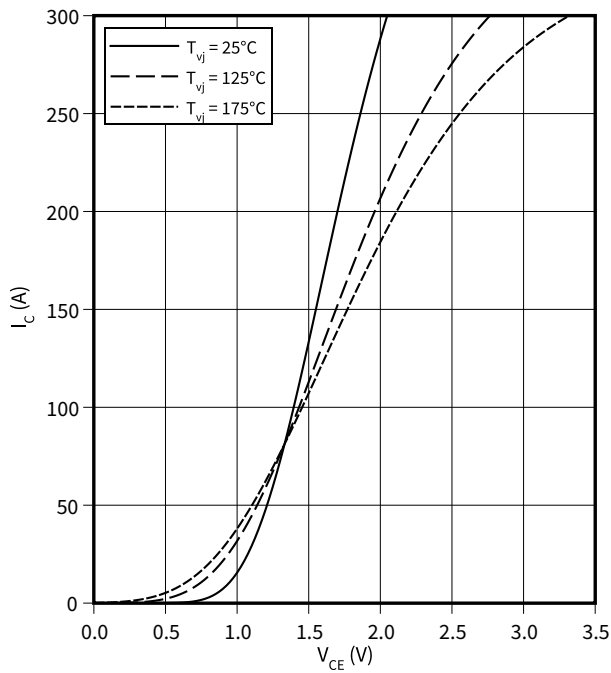
5 Characteristics diagrams

5 Characteristics diagrams

output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

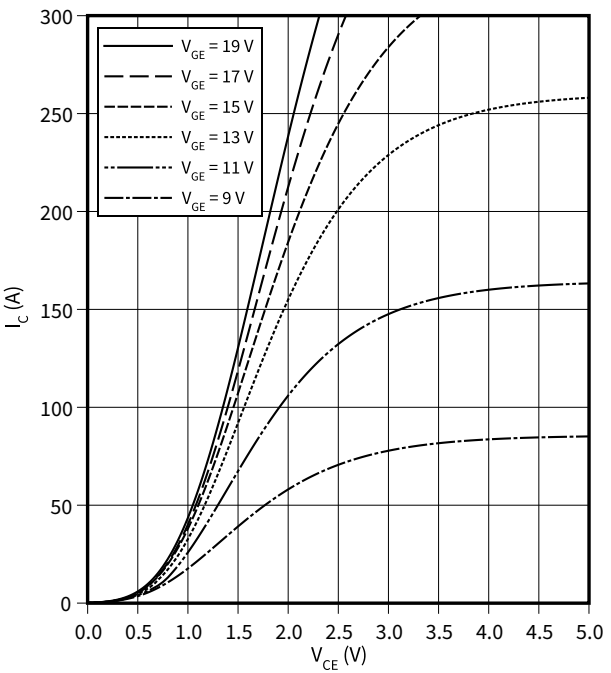
$V_{GE} = 15\text{ V}$



output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

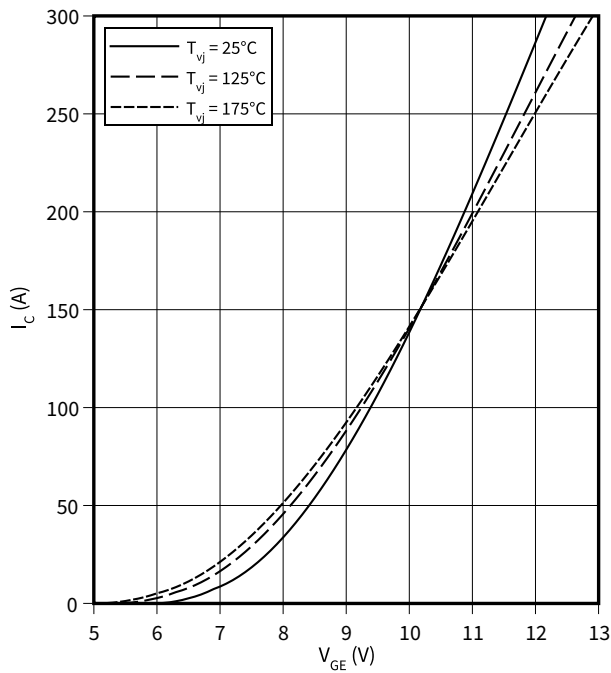
$T_{vj} = 175\text{ °C}$



transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

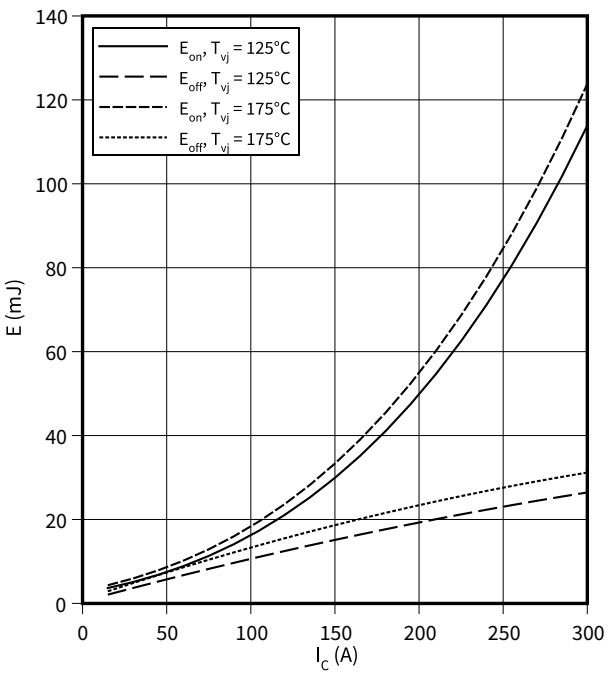
$V_{CE} = 20\text{ V}$



switching losses (typical), IGBT, Inverter

$E = f(I_C)$

$R_{Goff} = 3.5\text{ }\Omega$, $R_{Gon} = 3.5\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$, $V_{CE} = 600\text{ V}$

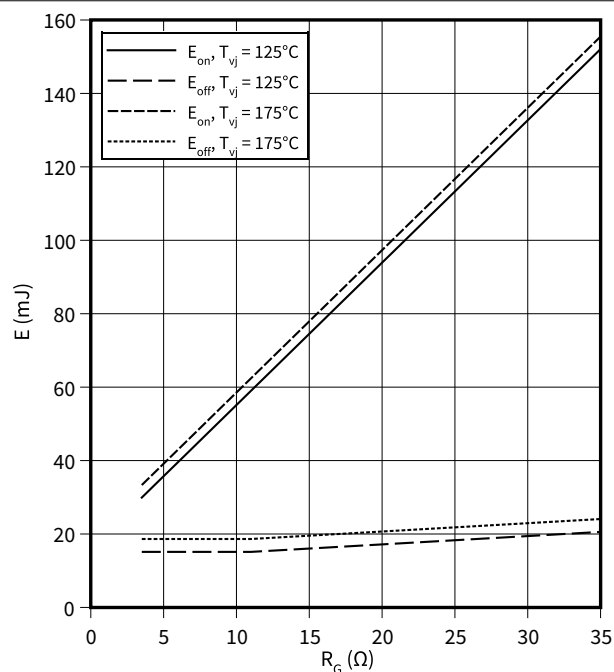


5 Characteristics diagrams

switching losses (typical), IGBT, Inverter

$$E = f(R_G)$$

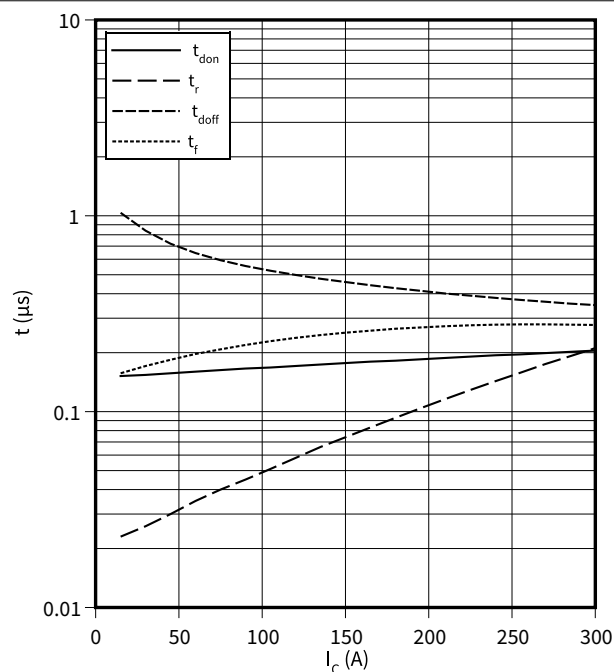
$$V_{GE} = \pm 15 \text{ V}, I_C = 150 \text{ A}, V_{CE} = 600 \text{ V}$$



switching times (typical), IGBT, Inverter

$$t = f(I_C)$$

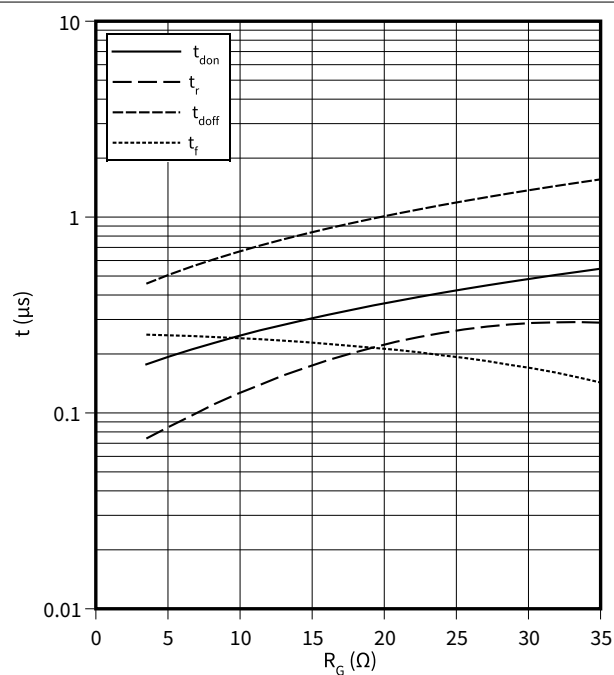
$$R_{Goff} = 3.5 \Omega, R_{Gon} = 3.5 \Omega, V_{GE} = \pm 15 \text{ V}, V_{CE} = 600 \text{ V}, T_{vj} = 175 \text{ °C}$$



switching times (typical), IGBT, Inverter

$$t = f(R_G)$$

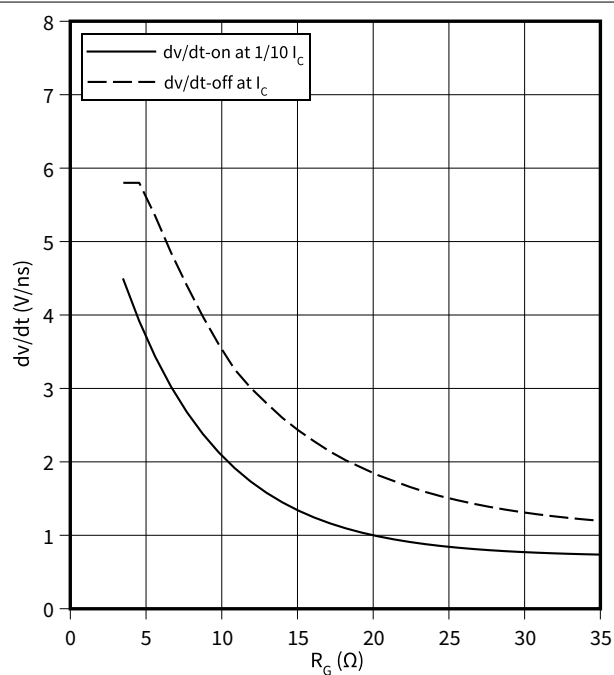
$$V_{GE} = \pm 15 \text{ V}, I_C = 150 \text{ A}, V_{CE} = 600 \text{ V}, T_{vj} = 175 \text{ °C}$$



Voltage slope (typical), IGBT, Inverter

$$dv/dt = f(R_G)$$

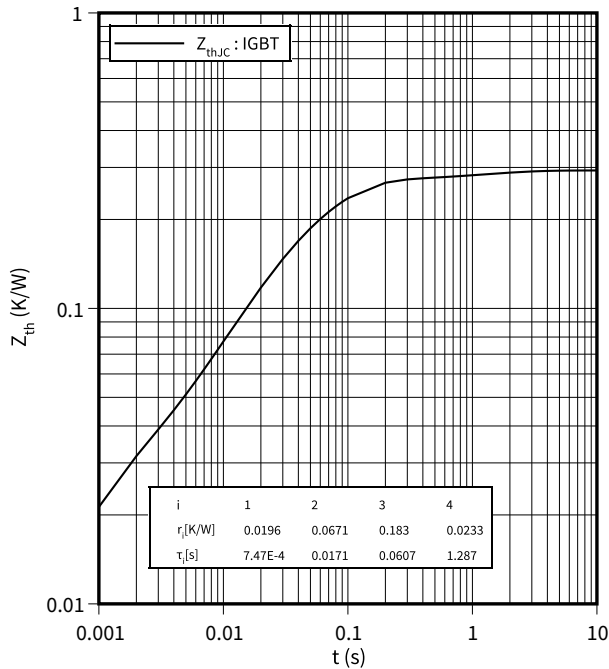
$$I_C = 150 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 25 \text{ °C}$$



5 Characteristics diagrams

transient thermal impedance , IGBT, Inverter

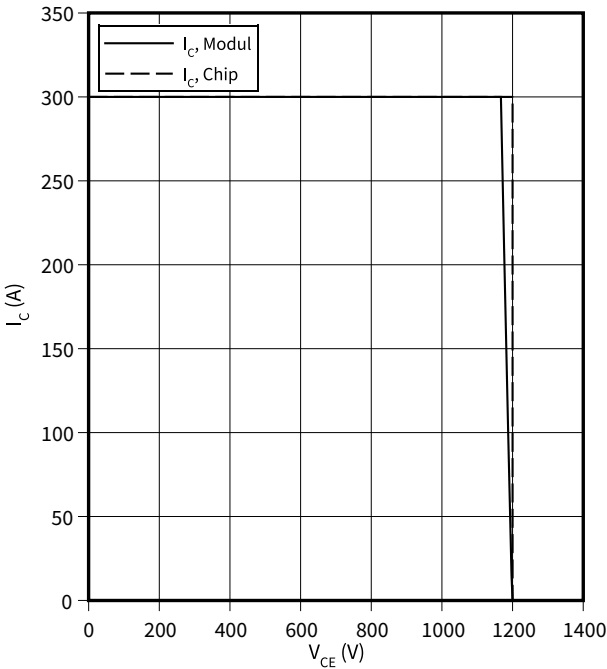
$Z_{th} = f(t)$



reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

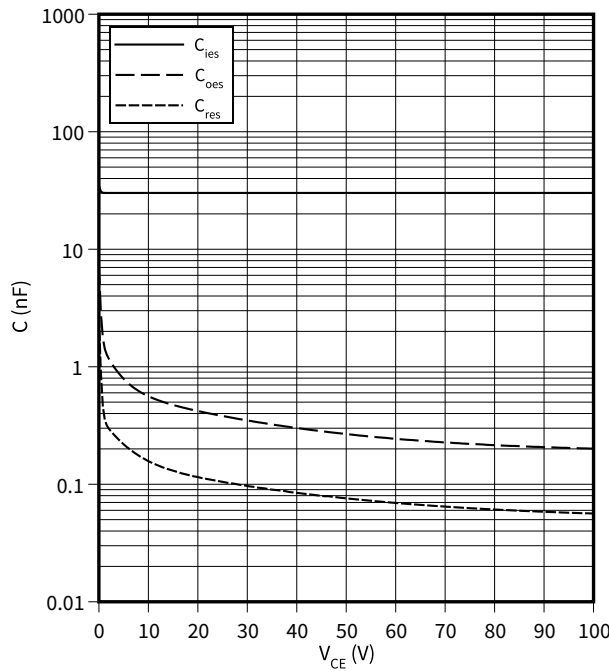
$R_{Goff} = 3.5 \Omega, V_{GE} = \pm 15 V, T_{vj} = 175 \text{ }^\circ\text{C}$



capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

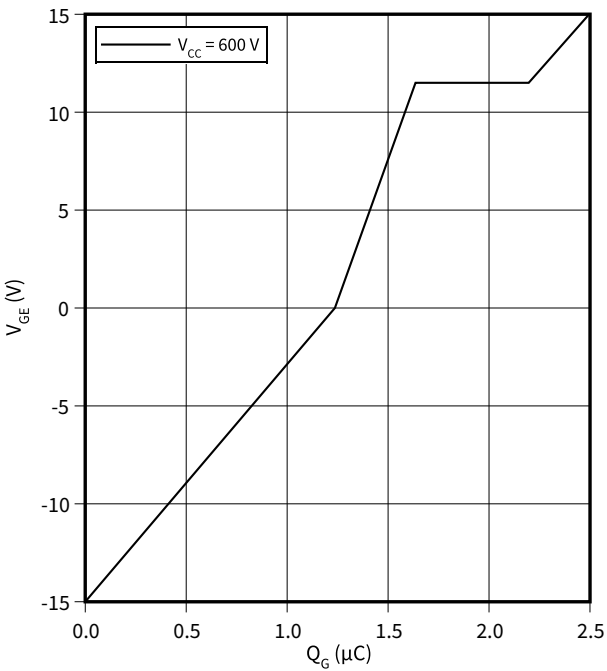
$f = 100 \text{ kHz}, V_{GE} = 0 V, T_{vj} = 25 \text{ }^\circ\text{C}$



gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$

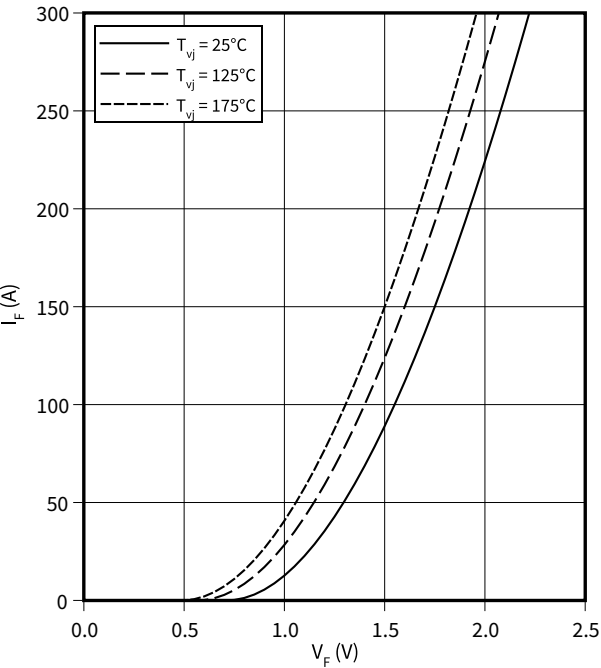
$I_C = 150 A, T_{vj} = 25 \text{ }^\circ\text{C}$



5 Characteristics diagrams

forward characteristic (typical), Diode, Inverter

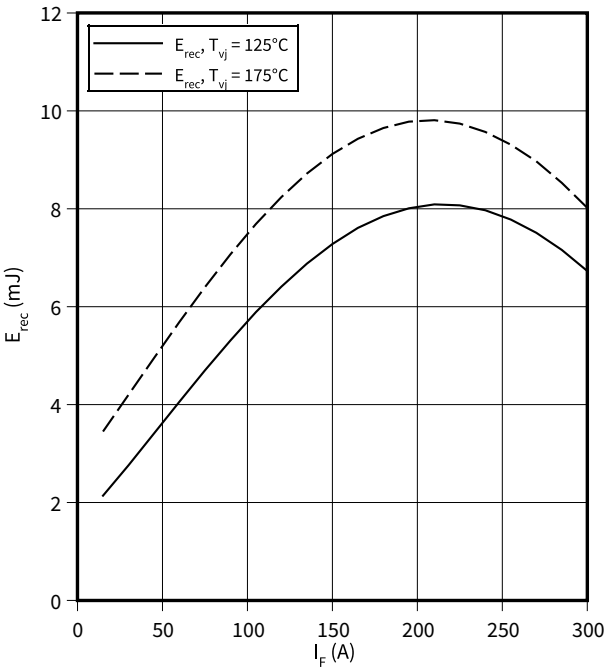
$I_F = f(V_F)$



switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

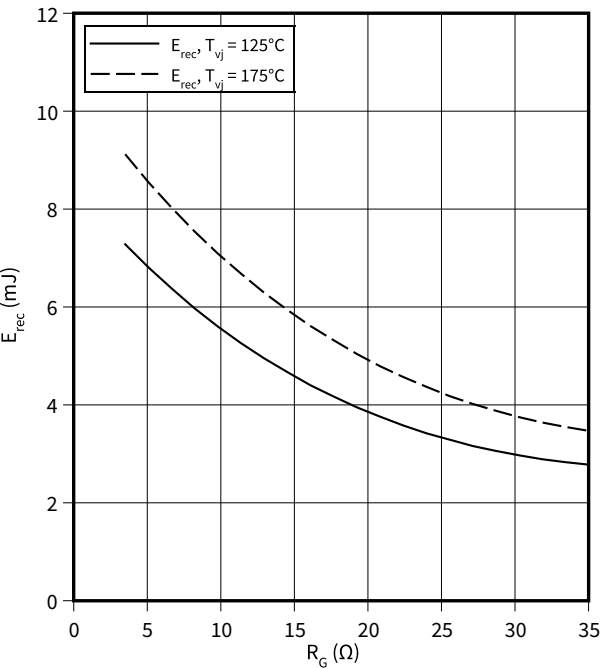
$R_G = 3.5\ \Omega, V_R = 600\ \text{V}$



switching losses (typical), Diode, Inverter

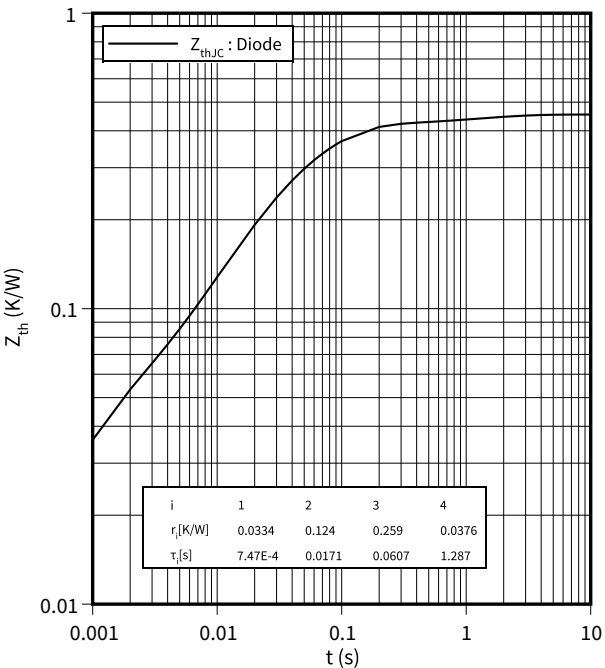
$E_{rec} = f(R_G)$

$I_F = 150\ \text{A}, V_R = 600\ \text{V}$



transient thermal impedance , Diode, Inverter

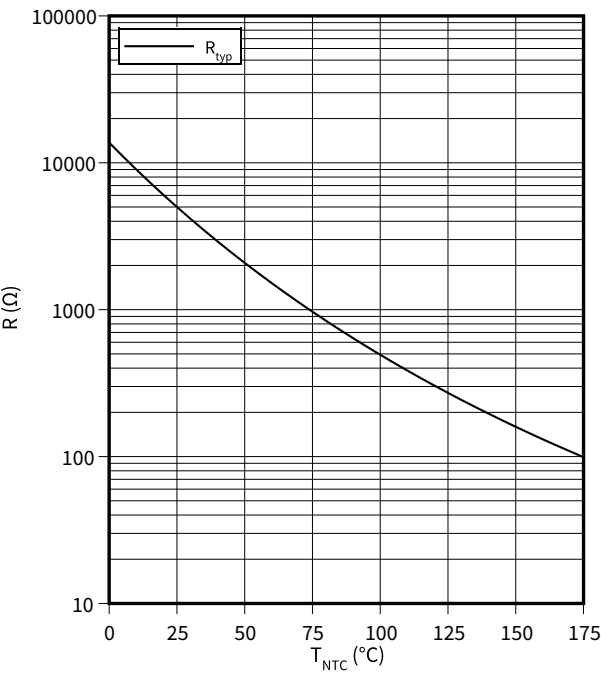
$Z_{th} = f(t)$



5 Characteristics diagrams

temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

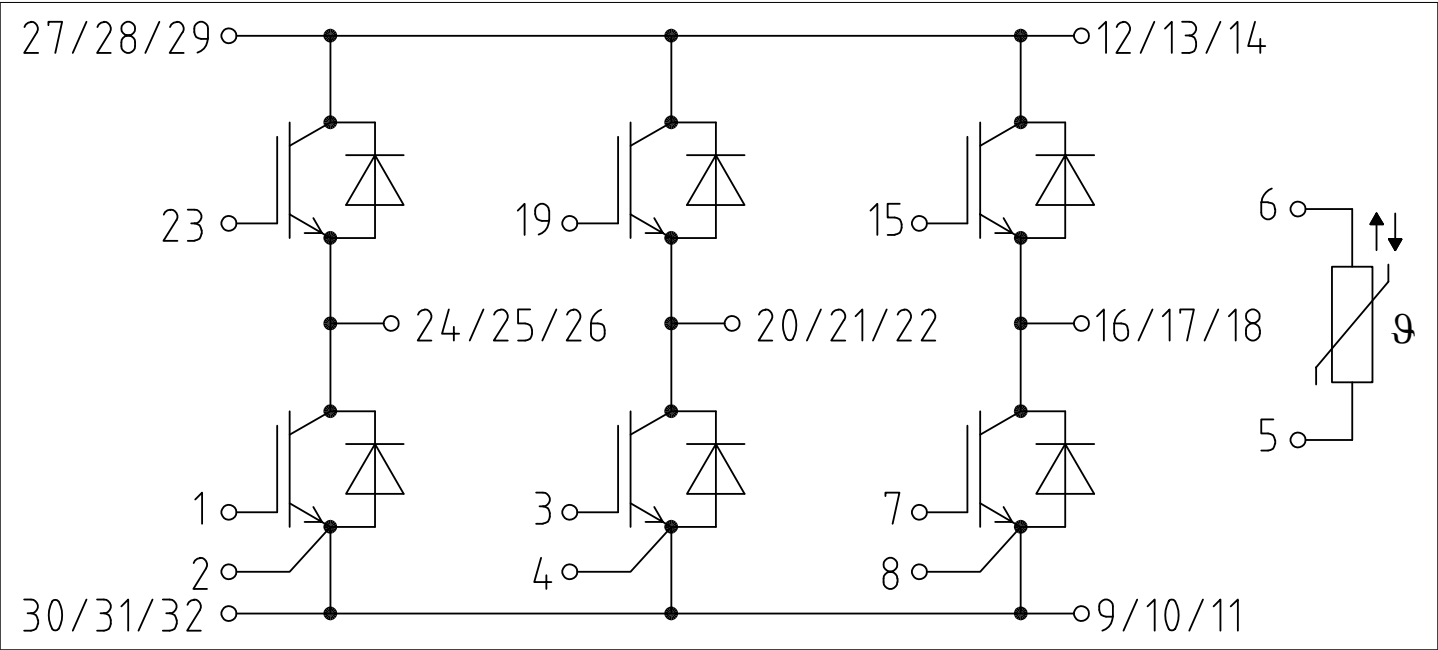


Figure 2

Figure 4

Revision history

Revision history

Document revision	Date of release	Description of changes
V1.0	2019-08-21	Target datasheet
1.00	2021-08-02	Final datasheet

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